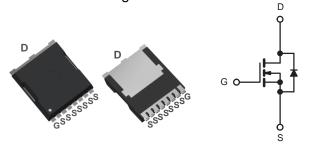


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N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	R _{DS(on)} (mΩ) TYP.	I _D (A)	Q _g (TYP.)			
100	1.9 at V _{GS} = 10 V	260	110 nC			

TOLL Pin Configuration



N-Channel MOSFET

FEATURES

- DT-Trench Power MOSFET
- 100 % R_g and UIS tested
- High Speed Power Switching

APPLICATIONS

- Power tools
- Synchronous rectification
- Hard Switching and High Speed Circuit
- DC/DCin Telecoms and Inductrial

ABSOLUTE MAXIMUM RATINGS ($T_c = 25 \text{ °C}$, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage	V _{DS}	100	v			
Gate-Source Voltage	V _{GS}	± 20	v			
	T _C = 25 °C		260			
Continuous Drain Current (T _J = 150 °C)	T _C = 100 °C	I _D	235	A		
Pulsed Drain Current (t = 100 µs)	I _{DM}	820	A			
Avalanche Current	L = 0.1 mH	I _{AS}	230			
Single Avalanche Energy ^a	L = 0.1 IIIA	E _{AS}	770	mJ		
Manimum Danner Diagin stien 2	T _C = 25 °C	- Pn -	340 ^b	w		
Maximum Power Dissipation ^a	T _C = 100 °C	۲D	170 ^b	vv		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C		

THERMAL RESISTANCE RATINGS							
PARAMETER			LIMIT	UNIT			
Junction-to-Ambient (PCB Mount) ^c	t ≤ 10 s	R _{thJA}	60	°C/W			
Junction-to-Case (Drain)	Steady State	R _{thJC}	0.45	C/W			

Notes

a. Duty cycle \leq 1 %.

b. See SOA curve for voltage derating.

c. When mounted on 1" square PCB (FR4 material).





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SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 V$, $I_D = 250 \mu A$		-	-	V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_{D}=250\;\mu A$	2	-	4	v	
Gate-Body Leakage	I _{GSS}	$V_{DS}=0~V,~V_{GS}=\pm~20~V$	-	-	± 100	nA	
Zero Gate Voltage Drain Current		$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	10		
Zero Gale Voltage Drain Gurrent	I _{DSS}	V_{DS} = 100 V, V_{GS} = 0 V, T_J = 100 $^\circ C$	-	-	100	μA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	260	-	-	А	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 25 \text{ A}$	-	1.9	2.5	mΩ	
Forward Transconductance ^a	g _{fs}	$V_{DS} = 5 V, I_D = 25 A$	-	75	-	S	
Dynamic ^b					•		
Input Capacitance	C _{iss}		-	7938	-	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 V, V_{DS} = 50 V, f = 1 MHz$	-	203	-		
Reverse Transfer Capacitance	C _{rss}		-	22	-		
Total Gate Charge ^c	Qg		-	110	-	nC	
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 25 \text{ A}$	-	26	-		
Gate-Drain Charge ^c	Q _{gd}		-	22	-		
Gate Resistance	R _g	f = 1 MHz	-	1.5	-	Ω	
Turn-On Delay Time ^c	t _{d(on)}		-	32	-		
Rise Time ^c	tr	V_{DD} = 50 V, I_D = 25 A, R_g = 6 Ω	-	25	-		
Turn-Off Delay Time ^c	t _{d(off)}	V _{GEN} = 10 V	-	49	-	ns	
Fall Time ^c	t _f		-	18	-		
Drain-Source Body Diode Ratings and	Characterist	ics ^b (T _C = 25 °C)					
Continuous Source-Drain Diode Current	ا _S	T _C = 25 °C	-	-	260	А	
Pulsed Current (t = 100 µs)	I _{SM}		-	-	800	А	
Forward Voltage ^a	V _{SD}	$I_F = 25 \text{ A}, \text{ V}_{GS} = 0 \text{ V}$	-	-	1.2	V	
Reverse Recovery Time	t _{rr}	I _F = 25 A, di/dt = 100 A/μs	-	78	-	ns	
Reverse Recovery Charge	Q _{rr}	$r_{\rm F} = 25 {\rm A}, {\rm d}_{\rm F} {\rm d}_{\rm F} = 100 {\rm A} {\rm \mu}{\rm s}$	-	160	-	nC	

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$

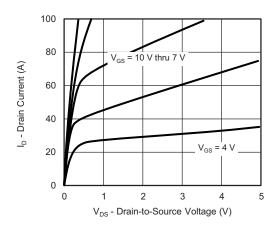
b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

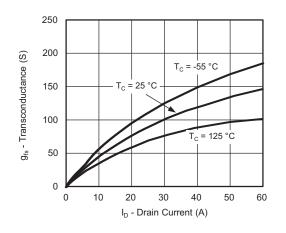
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



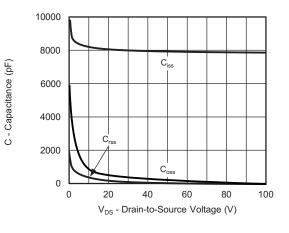
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



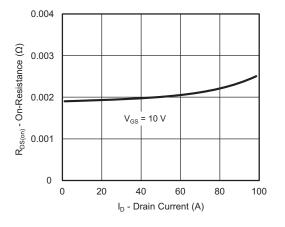
Output Characteristics



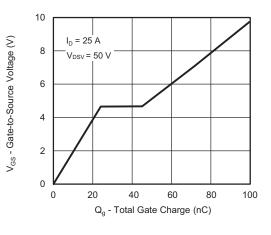
Transconductance



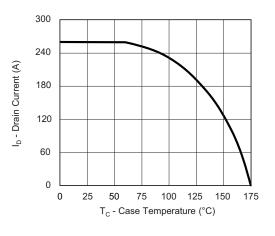
Capacitance



On-Resistance vs. Drain Current



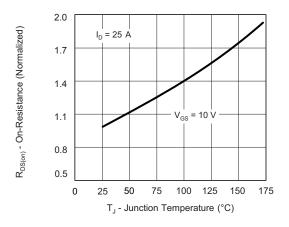
Gate Charge



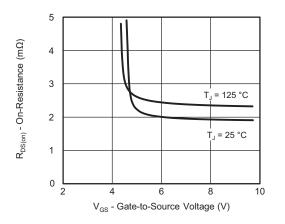
Current De-Rating



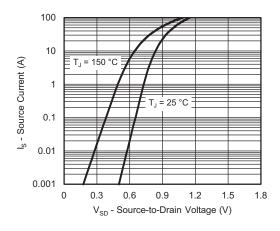
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



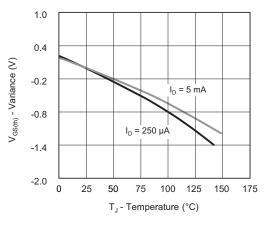
On-Resistance vs. Junction Temperature



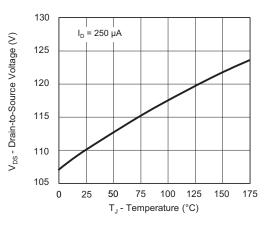
On-Resistance vs. Gate-to-Source Voltage



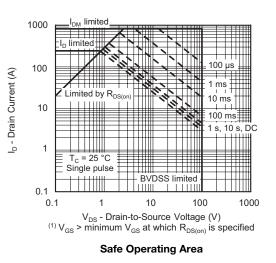
Source Drain Diode Forward Voltage



Threshold Voltage

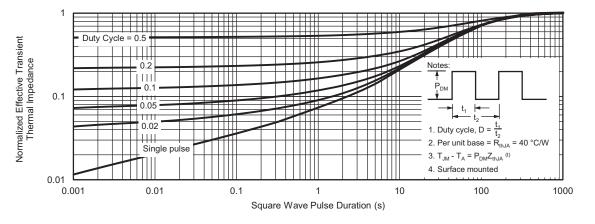


Drain Source Breakdown vs. Junction Temperature





THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)

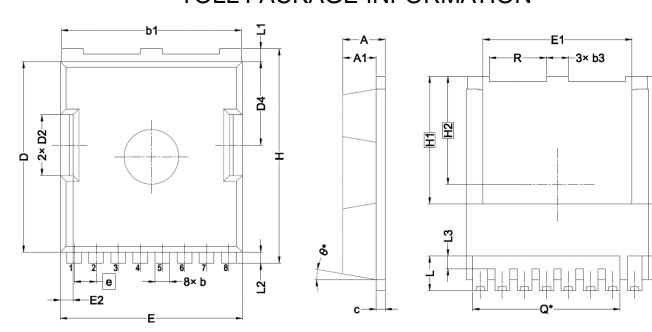


Normalized Thermal Transient Impedance, Junction-to-Ambient

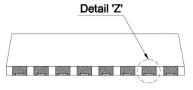
Din-Tek SEMICONDUCTOR

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TOLL PACKAGE INFORMATION



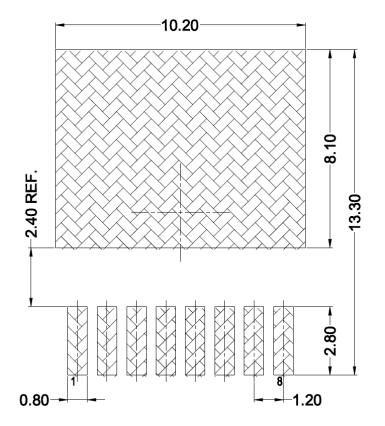


Detail 'Z'

SVMDOL	mm				mm		
SYMBOL	MIN	NOM	MAX	SYMBOL	MIN	NOM	MAX
Α	2.20	2.30	2.40	Н	11.58	11.68	11.78
A1	1.70	1.80	1.90	H1	6.95 BSC		
b	0.70	0.80	0.90	H2	5.89 BSC		
b1	9.70	9.80	9.90	i	0.10 REF		
b3	1.10	1.20	1.30	j	0.46 REF		
С	0.40	0.50	0.60	K	2.80 REF		
D	10.28	10.38	10.48	L	1.40 1.90 2.10		2.10
D1	10.98	11.08	11.18	L1	0.60	0.70	0.80
D2	3.20	3.30	3.40	L2	0.50	0.60	0.70
D4	4.45	4.55	4.65	L3	0.30	0.70	0.80
E	9.80	9.90	10.00	N	8		
E1	8.00	8.10	8.20	Q	8.00 REF		
E2	0.60	0.70	0.80	R	3.00	3.10	3.20
е	e 1.20 BSC			θ	10º REF		



TOLL RECOMMENDED LAND PATTERN



unit : mm



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